PRELIMINARY DATA SHEET

LASER DIODE NX8560LJ-CC

EA MODULATOR INTEGRATED 1 550 nm MQW-DFB LASER DIODE MODULE FOR 10 Gb/s APPLICATIONS

DESCRIPTION

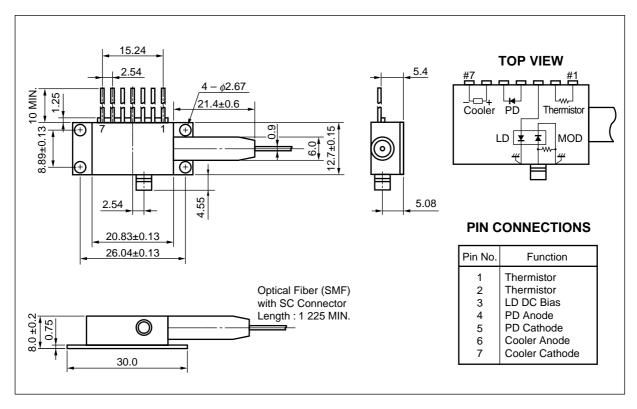
NEC

The NX8560LJ-CC is an Electro-Absorption (EA) modulator integrated, 1 550 nm Multiple Quantum Well (MQW) structured Distributed Feed-Back (DFB) laser diode. It is capable of transmitting up to 40 km (dispersion: 800 ps/nm) for 10 Gb/s applications by using standard fiber.

***** FEATURES

- Integrated electroabsorption modulator
- Up to 40 km transmission 10 Gb/s (dispersion: 800 ps/nm)
- Low modulation voltage
- 7-pin butterfly package with GPO[™] connector
- Available for DWDM wavelengths based on ITU-T recommendations
- Butterfly package with SC-UPC connector

* PACKAGE DIMENSIONS (UNIT: mm, unless otherwise specified ±0.2 mm)

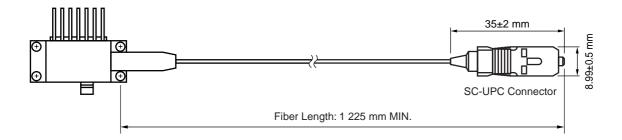


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The mark **★** shows major revised points.

OPTICAL FIBER CHARACTERISTICS

Parameter	Specification	Unit
Mode Field Diameter	9.3±0.5	μm
Cladding Diameter	125±1	μm
Tight Buffer Diameter	900±100	μm
Cut-off Wavelength	< 1 270	nm
Attenuation 1 525 to 1 575 nm	< 0.3	dB/km
Minimum Fiber Bending Radius	30	mm
Fiber Length	1 225 MIN.	mm
Flammability	UL1581 VW-1	



★ ORDERING INFORMATION: Wavelength is a certain point between 1 530 nm and 1 563 nm @ TLD = Tset (SC-UPC Connector)

Part Number	Available Connector
NX8560LJ-CC	With SC-UPC Connector

* ORDERING INFORMATION: Wavelength on ITU-T grid @ TLD = Tset

Part Number	ITU-T Wavelength ¹	Frequency
With SC-UPC Connector	(nm)	(THz)
NX8560LJ303-CC	1530.33	195.90
NX8560LJ311-CC	1531.11	195.80
NX8560LJ318-CC	1531.89	195.70
NX8560LJ326-CC	1532.68	195.60
NX8560LJ334-CC	1533.46	195.50
NX8560LJ342-CC	1534.25	195.40
NX8560LJ350-CC	1535.03	195.30
NX8560LJ358-CC	1535.82	195.20
NX8560LJ366-CC	1536.60	195.10
NX8560LJ373-CC	1537.39	195.00
NX8560LJ381-CC	1538.18	194.90
NX8560LJ389-CC	1538.97	194.80
NX8560LJ397-CC	1539.76	194.70
NX8560LJ405-CC	1540.55	194.60
NX8560LJ413-CC	1541.35	194.50
NX8560LJ421-CC	1542.14	194.40
NX8560LJ429-CC	1542.93	194.30
NX8560LJ437-CC	1543.73	194.20
NX8560LJ445-CC	1544.52	194.10
NX8560LJ453-CC	1545.32	194.00
NX8560LJ461-CC	1546.11	193.90
NX8560LJ469-CC	1546.91	193.80
NX8560LJ477-CC	1547.71	193.70
NX8560LJ485-CC	1548.51	193.60
NX8560LJ493-CC	1549.31	193.50
NX8560LJ501-CC	1550.11	193.40
NX8560LJ509-CC	1550.91	193.30
NX8560LJ517-CC	1551.72	193.20
NX8560LJ525-CC	1552.52	193.10

*1 The value which omitted and computed the 3rd place below the decimal point

Part Number	ITU-T Wavelength ^{*1}	Frequency
With SC-UPC Connector	(nm)	(THz)
NX8560LJ533-CC	1553.32	193.00
NX8560LJ541-CC	1554.13	192.90
NX8560LJ549-CC	1554.94	192.80
NX8560LJ557-CC	1555.74	192.70
NX8560LJ565-CC	1556.55	192.60
NX8560LJ573-CC	1557.36	192.50
NX8560LJ581-CC	1558.17	192.40
NX8560LJ589-CC	1558.98	192.30
NX8560LJ597-CC	1559.79	192.20
NX8560LJ606-CC	1560.60	192.10
NX8560LJ614-CC	1561.41	192.00
NX8560LJ622-CC	1562.23	191.90
NX8560LJ630-CC	1563.04	191.80

*1 The value which omitted and computed the 3rd place below the decimal point

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Optical Output Power from Fiber	Pf	10	mW
Forward Current of LD	IFLD	150	mA
Reverse Voltage of LD	Vrld	2.0	V
Forward Voltage of Modulator	Vfea	1	V
Reverse Voltage of Modulator	Vrea	4	V
Forward Current of PD	IFPD	1	mA
Reverse Voltage of PD	Vrpd	10	V
Cooler Current	lc	1.5	А
Cooler Voltage	Vc	2.5	V
Operating Case Temperature	Tc	-20 to +70	°C
Storage Temperature	Tstg	-40 to +85	°C
Lead Soldering Temperature	Tsld	260 (10 sec.)	°C

★ ELECTRO-OPTICAL CHARACTERISTICS

(TLD = 25°C, Tc = 25°C, BOL, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Laser Set Temperature	Tset	*1	20		35	°C
Operating Current	lop	TLD = Tset	50	60	80	mA
Modulation Center Voltage	Vcenter		-2.0		-0.5	V
Modulation Voltage	Vmod		2.0		3.0	V
Forward Voltage of LD	VFLD	IFLD = Iop			2.0	V
Threshold Current	Ith	TLD = Tset		6	20	mA
Optical Output Power from Fiber	Pf	Under modulation ^{*2}	-1.0			dBm
Peak Emission Wavelength	λρ	$I_{FLD} = I_{op}, V_{EA} = O \; V, T_{LD} = T_{set}$	1 530	ITU-T [∗] 3	1 563	nm
Side Mode Suppression Ratio	SMSR	$I_{FLD} = I_{op}, V_{EA} = 0 V$	30			dB
Extinction Ratio	ER	Under modulation ²	10	11		dB
Rise Time	tr	20-80%, Under modulation ^{*2}			40	ps
Fall Time	tr	80-20%, Under modulation ^{*2}			40	ps
Dispersion Penalty	DP	40 km SMF under modulation ^{*2,4}			2.0	dB
Optical Isolation	ls		23			dB
Input Return Loss	S11	$I_{FLD} = I_{op}, V_{EA} = -1 V,$ f = 130 MHz to 5 GHz		-10	-8	dB
		$I_{FLD} = I_{op}, V_{EA} = -1 V,$ f = 5 GHz to 10 GHz		-8	-5	

*1 NX8560LJ-CC $$: T_{set}$ is a certain point between 20^{\circ}C and 35^{\circ}C $$

NX8566LJxxx-CC : Tset is set at a certain point between 20°C and 35°C for ITU-T grid wavelength

*2 40 km SMF under modulation, 9.95328 Gb/s, PRBS 2²³–1, VEA = Vcenter ± 1/2Vmod, IFLD = Iop, TLD = Tset, NEC Test System

- V_{center} : a certain point between –0.5 V and –1.5 V
- V_{mod} : a certain point between 2 V and 3 V
- Iop : a certain point between 50 mA and 80 mA
- *3 Available for DWDM wavelengths based on ITU-T recommendations (100 GHz grid).

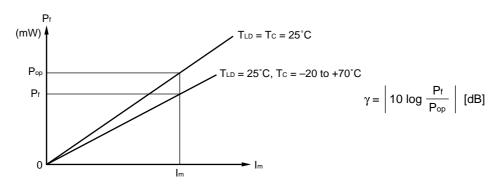
Please refer to ORDERING INFORMATION.

*4 BER = 10^{-10}

ELECTRO-OPTICAL CHARACTERISTICS (Applicable to Monitor PD: TLD = 25°C, Tc = -20 to +70°C)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*	Monitor Current	lm	$V_{\text{RPD}} = 5 \text{ V}, \text{ Ifld} = \text{I}_{\text{op}}, \text{ Vea} = 0 \text{ V}$	30		1 100	μA
*	Dark Current	lo	$V_{RPD} = 5 V, V_{EA} = 0 V$			10	nA
	Terminal Capacitance	Ct	$V_{RPD} = 5 V, f = 1 MHz$			15	pF
	Tracking Error	γ ^{*1}	I _m = const.			0.5	dB

*1 Tracking Error: γ



ELECTRO-OPTICAL CHARACTERISTICS (Applicable to Thermistor and TEC: $T_{LD} = 25^{\circ}C$, $T_{C} = -20$ to $+70^{\circ}C$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Thermistor Resistance	R	TLD = 25°C	9.5	10.0	10.5	kΩ
B Constant	В		3 350	3 450	3 550	К
Cooler Current	lc	∆T = 50°C			1.2	А
Cooler Voltage	Vc	⊿T = 50°C			2.4	V

EXTINCTION RATIO vs. MODULATOR VOLTAGE

1

Revers Voltage of Modulator VREA (V)

2

3

0

5

10

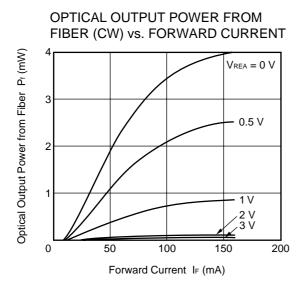
15

20

25∟ 0

Extinction Ratio ER (dB)

* TYPICAL CHARACTERISTICS (TLD = 25°C, unless otherwise specified)





DFB-LD FAMILY

		Absolute Rati	Maximum ings	Electro-Optical Characteristics $(Tc = 25^{\circ}C)$				
	Part Number	Тс (°С)	T₅tg (°C)	Ith (mA)	P _f (mW)	λ _Ρ (nm)	Application	Package
				TYP.	MIN.	TYP.		
	NX8300BE-CC NX8300CE-CC	0 to +75	-40 to +85	15	2*1	1 310	2.5 Gb/s: STM-16 (S-16.1, L-16.1)	Coaxial
	NX8303BG-CC NX8303CG-CC	-10 to +85	-40 to +85	15	2*1	1 310	622 Mb/s: STM-4 (L-4.1)	Coaxial
	NX8503BG-CC NX8503CG-CC	-10 to +85	-40 to +85	15	2*1	1 550	156 Mb/s: STM-1 (L-1.2, L-1.3)	Coaxial
							622 Mb/s: STM-4 (L-4.2, L-4.3)	
	NX8504BE-CC NX8504CE-CC	-10 to +85	-40 to +85	15	2"	1 550	622 Mb/s: STM-4 (L-4.2, L-4.3)	Coaxial
*	NX8560LJ-CC	-20 to +70	-40 to +85	6	−1 dBm	1 550 ^{*2}	≤ 10 Gb/s: STM-64	BFY with GPO
	NX8562LB	-20 to +65	-40 to +85	20	20	1 550 ^{*2}	CW Light Source for external modulator	BFY
	NX8563LB	-20 to +65	-40 to +85	20	10	1 550 ^{*2}	CW Light Source for external modulator	BFY
*	NX8564LE-CC	-20 to +70	-40 to +85	7	–2 dBm ^{*1}	1 550 ^{*2}	2.5 Gb/s: STM-16, 360 km EA modulator integrated	BFY
*	NX8565LE-CC	-20 to +70	-40 to +85	7	–2 dBm ^{*1}	1 550 ^{*2}	2.5 Gb/s: STM-16, 600 km EA modulator integrated	BFY
*	NX8566LE-CC	-20 to +70	-40 to +85	7	0 dBm	1 550 ^{*2}	2.5 Gb/s: STM-16, 240 km EA modulator integrated	BFY
*	NX8570 Series	-20 to +70	-40 to +85	20	20	1 550 ^{*2}	CW Light Source with λ monitoring PD	BFY
*	NX8571 Series	-20 to +70	-40 to +85	20	10	1 550 ^{*2}	CW Light Source with λ monitoring PD	BFY

*1 TYP.

 $^{\ast}\mathbf{2}$ Available for DWDM Wavelengths based on ITU-T recommendations

REFERENCE

Document Name	Document No.
Optical semiconducrtor devices for fiberoptic communications Selection Guide	P12480E
Opto-Electronics Devices Pamphlet	P13623E
Opto-Electronics Devices (CD-ROM)	P12944X
NEC semiconductor device reliability/quality control system ^{*1}	C11159E
Quality grades on NEC semiconductor devices ¹⁴	C11531E
SEMICONDUCTOR SELECTION GUIDE –Products and Packages– ^M	X13769E

*1 Published by NEC Corporation

 PATENT USP 4,826,295 CA 1,286,848 EP 143 000

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M8E 00.4-0110

SAFETY INFORMATION ON THIS PRODUCT



SEMICONDUCTOR LASER					
	\square				
AVOID E	XPOSURE-Invisible				
Laser Radiation is emitted from					
this apert	ure				

Warning Laser Beam	A laser beam is emitted from this diode during operation. The laser beam, visible or invisible, directly or indirectly, may cause injury to the eye or loss of eyesight.
	Do not look directly into the laser beam.
	Avoid exposure to the laser beam, any reflected or collimated beam.
Caution GaAs Products	The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.
	Do not destroy or burn the product.
	Do not cut or cleave off any part of the product.
	Do not crush or chemically dissolve the product.
	Do not put the product in the mouth.
	Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.
Caution Optical Fiber	A glass-fiber is attached on the product. Handle with care.When the fiber is broken or damaged, handle carefully to avoid injury from the damaged part or fragments.

▶Business issue

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► Technical issue

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